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GaAs SMT pHEMT DUAL CHANNEL LOW NOISE AMPLIFIER, 1.7 - 2.2 GHz

Typical Applications

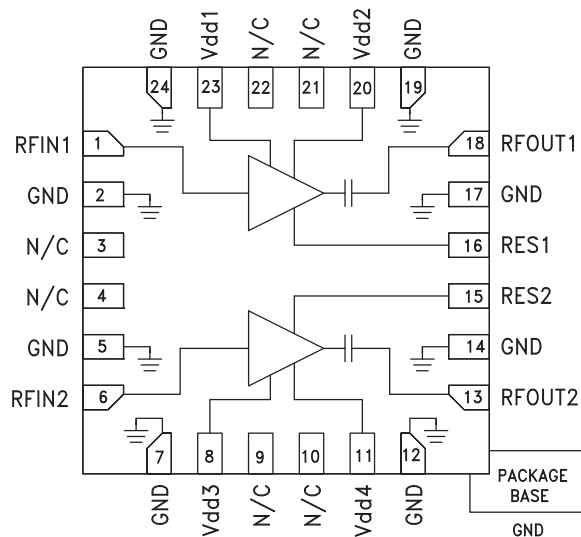
The HMC818LP4E is ideal for:

- Cellular/3G and LTE/WiMAX/4G
- BTS & Infrastructure
- Repeaters and Femtocells
- Public Safety Radios

Features

- Low Noise Figure: 0.85 dB
- High Gain: 20.5 dB
- High OIP3: +35 dBm
- Single Supply: +3V to +5V
- 50 Ohm Matched Input/Output
- 24 Lead 4x4mm QFN Package: 16mm²

Functional Diagram



General Description

The HMC818LP4E is a GaAs pHEMT Dual Channel Low Noise Amplifier that is ideal for Cellular/3G and LTE/WiMAX/4G basestation front-end receivers operating between 1.7 - 2.2 GHz. The amplifier has been optimized to provide 0.85 dB noise figure, 20.5 dB gain and +35 dBm output IP3 from a single supply of +5V. Input and output return losses are excellent and the LNA requires minimal external matching and bias decoupling components. The HMC818LP4E can be biased with +3V to +5V and features an externally adjustable supply current which allows the designer to tailor the linearity performance of each channel of the LNA for a specific application.

Electrical Specifications,

$T_A = +25^\circ C$, $R_{bias} = 10K$, $V_{dd} = V_{dd1}, 2, 3, 4$, $I_{dd} = I_{dd1} + I_{dd2}, I_{dd3} + I_{dd4}$

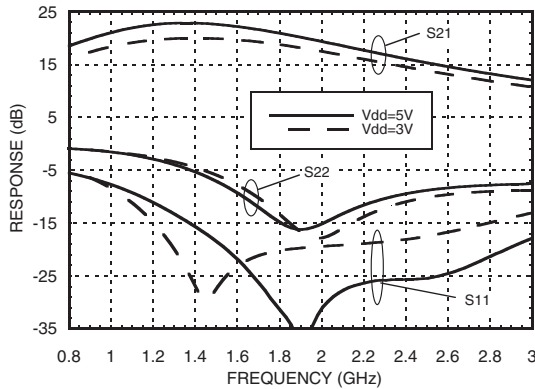
| Parameter | Vdd = 3V | | | | | | Vdd = 5V | | | | | | Units |
|--|-------------|-------|------|-------------|-------|------|-------------|-------|------|-------------|-------|------|-------|
| | Min. | Typ. | Max. | Min. | Typ. | Max. | Min. | Typ. | Max. | Min. | Typ. | Max. | |
| Frequency Range | 1700 - 2000 | | | 2000 - 2200 | | | 1700 - 2000 | | | 2000 - 2200 | | | MHz |
| Gain | 15 | 18 | | 14 | 16.5 | | 17 | 20.5 | | 15.5 | 17.5 | | dB |
| Gain Variation Over Temperature | | 0.010 | | | 0.008 | | | 0.015 | | | 0.012 | | dB/°C |
| Noise Figure | | 0.95 | 1.2 | | 0.95 | 1.2 | | 0.85 | 1.1 | | 0.85 | 1.1 | dB |
| Input Return Loss | | 18 | | | 17 | | | 21 | | | 18 | | dB |
| Output Return Loss | | 16 | | | 15 | | | 15 | | | 13 | | dB |
| Output Power for 1 dB Compression (P1dB) | | 14 | | | 15 | | | 19 | | | 21 | | dBm |
| Saturated Output Power (Psat) | | 15 | | | 16 | | | 20 | | | 21.5 | | dBm |
| Output Third Order Intercept (IP3) | | 24.5 | | | 25 | | | 33 | | | 35 | | dBm |
| Supply Current (Idd) | 30 | 42 | 55 | 30 | 42 | 55 | 78 | 112 | 146 | 78 | 112 | 146 | mA |

* Rbias resistor sets current, see application circuit herein

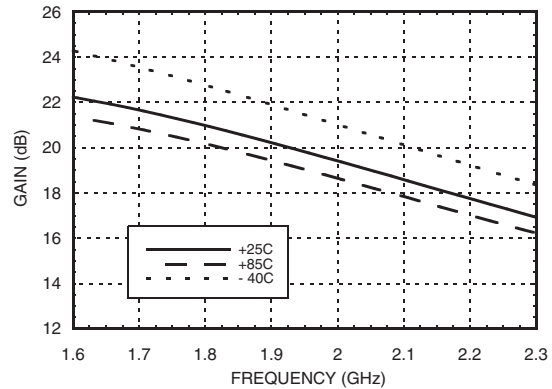


**GaAs SMT pHEMT DUAL CHANNEL
LOW NOISE AMPLIFIER, 1.7 - 2.2 GHz**

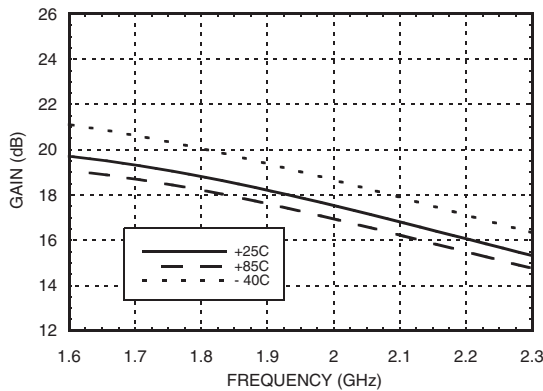
Broadband Gain & Return Loss^{[1] [2]}



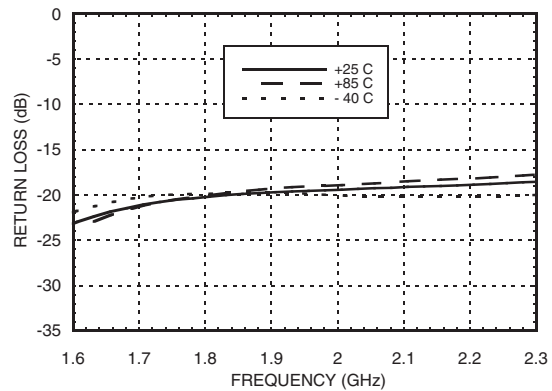
Gain vs. Temperature^[1]



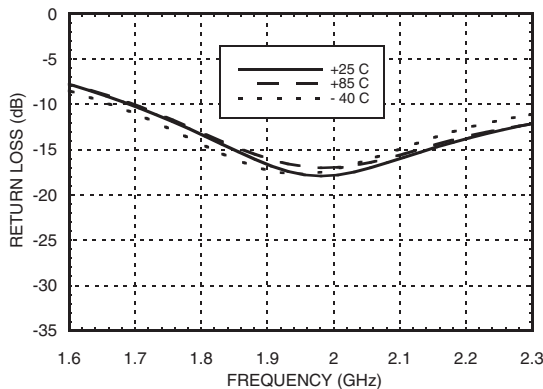
Gain vs. Temperature^[2]



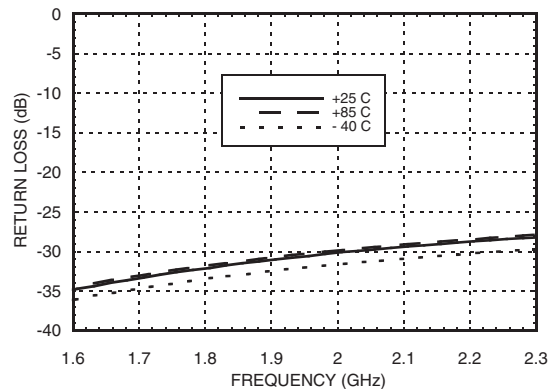
Input Return Loss vs. Temperature^[1]



Output Return Loss vs. Temperature^[1]



Reverse Isolation vs. Temperature^[1]



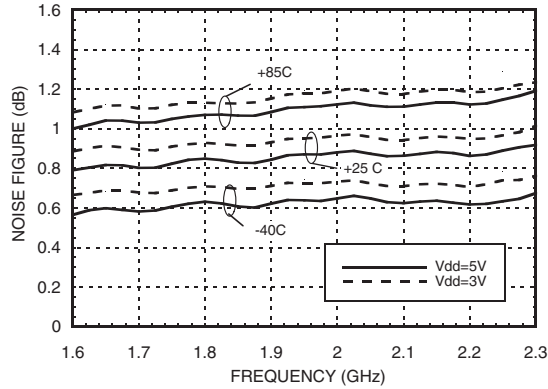
[1] Vdd = 5V, Rbias = 10K [2] Vdd = 3V, Rbias = 10K

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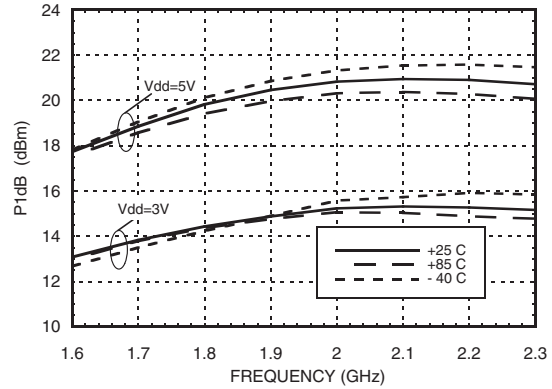
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AMPLIFIERS - LOW NOISE - SMT

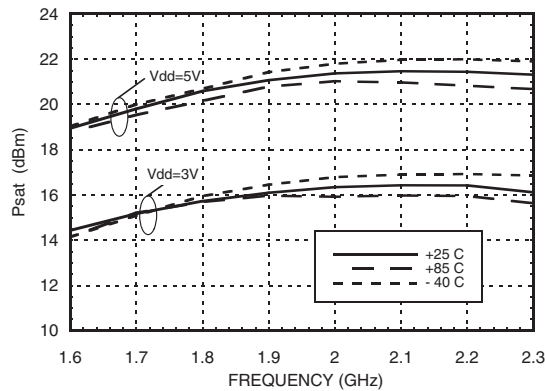
Noise Figure vs Temperature [1]



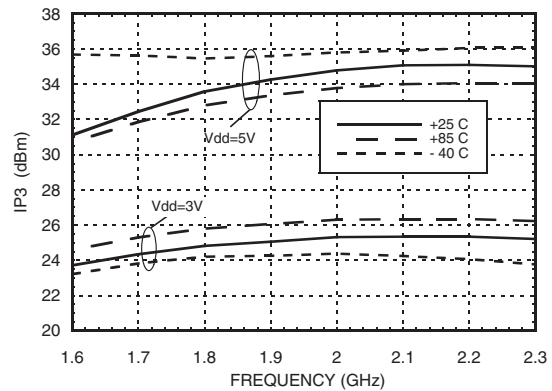
Output P1dB vs. Temperature



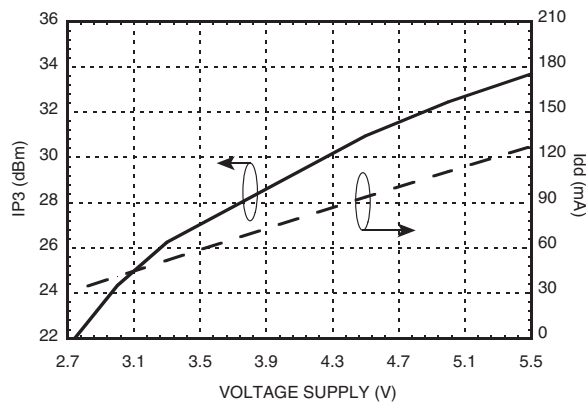
Psat vs. Temperature



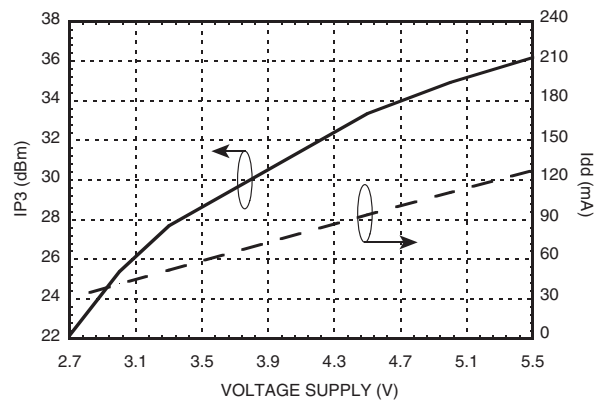
Output IP3 vs. Temperature



Output IP3 and Idd vs. Supply Voltage @ 1700 MHz



Output IP3 and Idd vs. Supply Voltage @ 2100 MHz

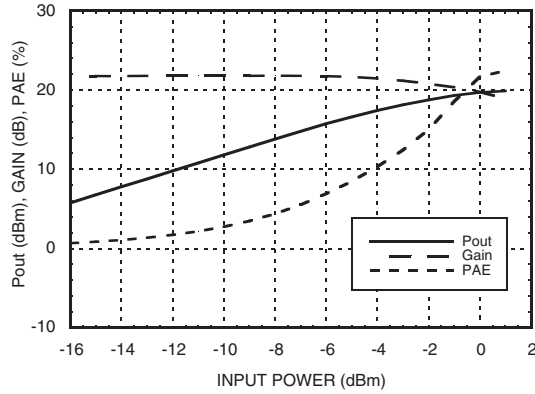


[1] Measurement reference plane shown on evaluation PCB drawing.

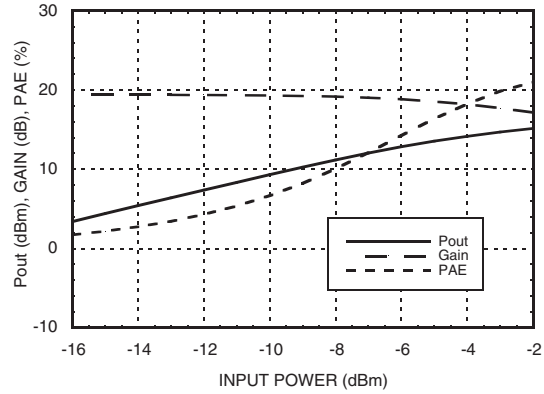


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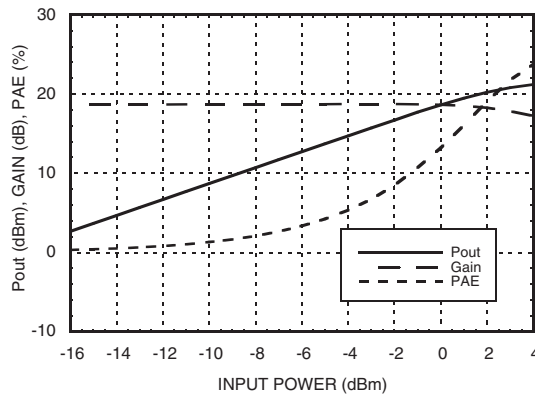
Power Compression @ 1700 MHz [1]



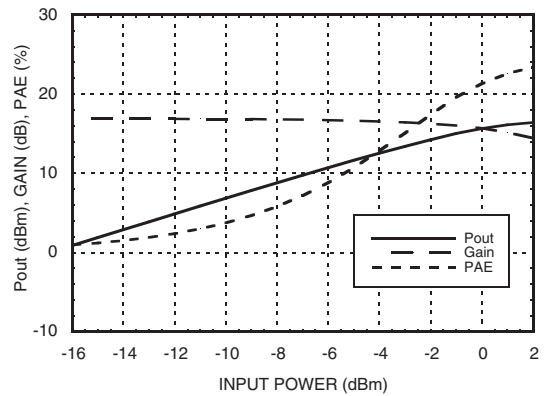
Power Compression @ 1700 MHz [2]



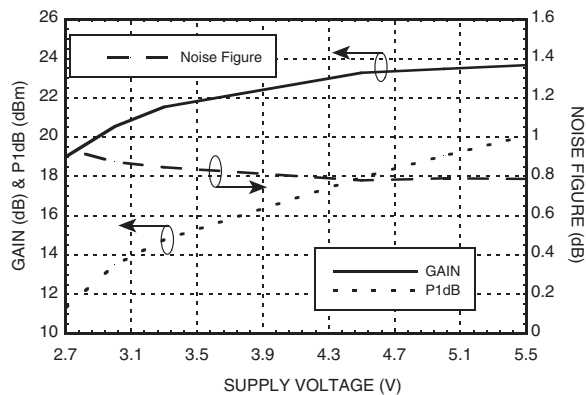
Power Compression @ 2100 MHz [1]



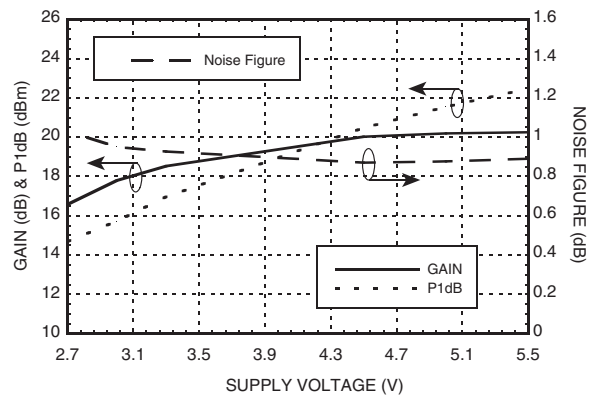
Power Compression @ 2100 MHz [2]



**Gain, Power & Noise Figure vs.
Supply Voltage @ 1700 MHz**



**Gain, Power & Noise Figure vs.
Supply Voltage @ 2100 MHz**



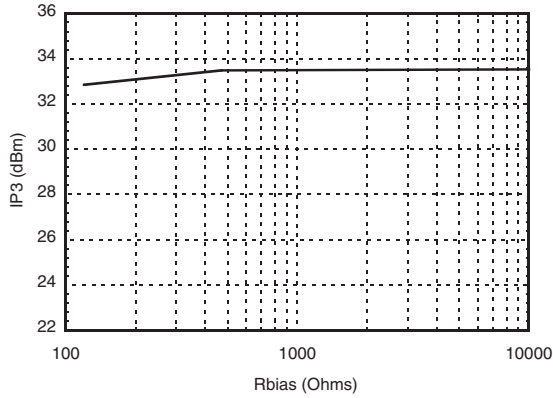
[1] Vdd = 5V [2] Vdd = 3V

GaAs SMT pHEMT DUAL CHANNEL LOW NOISE AMPLIFIER, 1.7 - 2.2 GHz

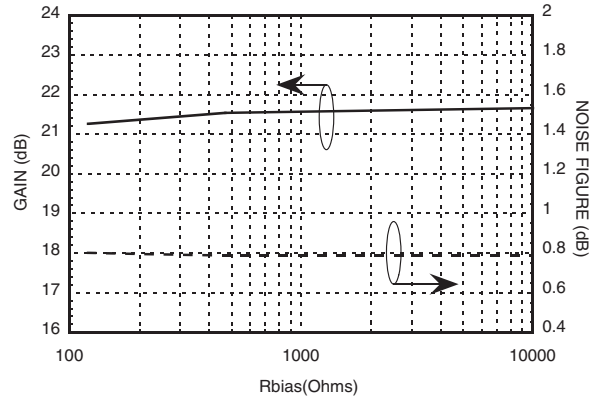
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AMPLIFIERS - LOW NOISE - SMT

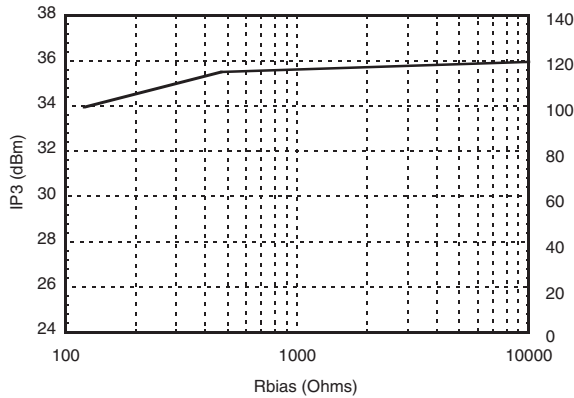
Output IP3 vs. Rbias @ 1700 MHz [1]



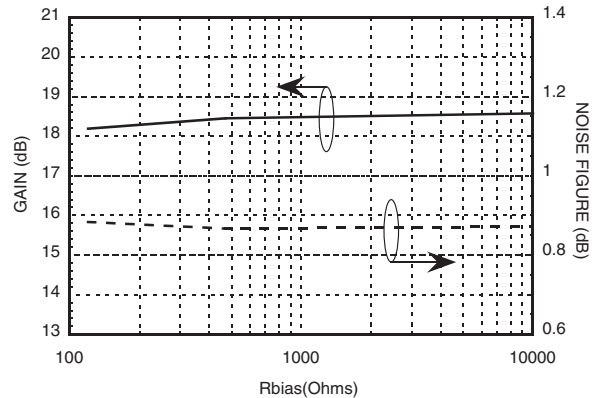
Gain, Noise Figure & Rbias @ 1700 MHz [1]



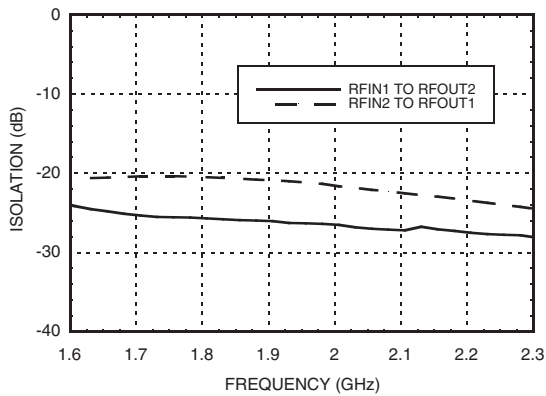
Output IP3 vs. Rbias @ 2100 MHz [1]



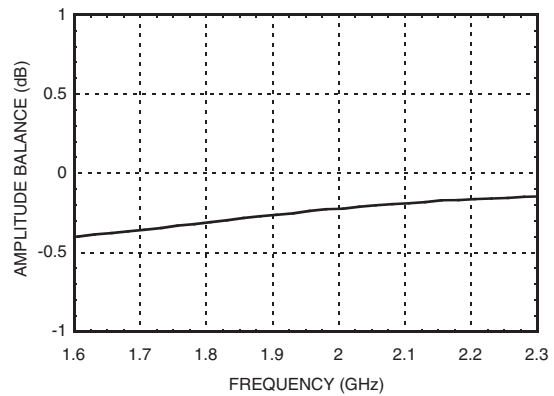
Gain, Noise Figure & Rbias @ 2100 MHz [1]



Cross Channel Isolation [1]



Magnitude Balance [1]

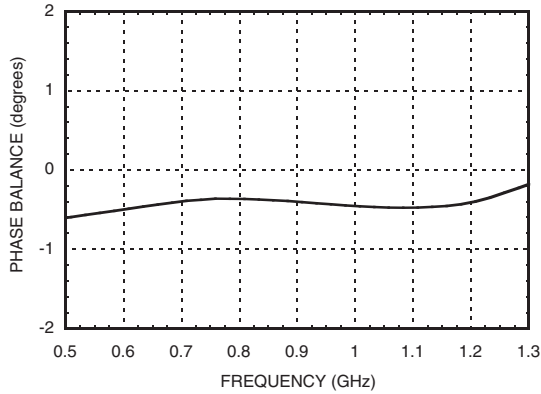


[1] Vdd = 5V



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Phase Balance [1]



Absolute Bias Resistor

Range & Recommended Bias Resistor Values for Idd

| Vdd (V) | Rbias | | | Idd (mA) |
|---------|------------|--------------|-----------|----------|
| | Min (Ohms) | Max (Ohms) | R1 (Ohms) | |
| 3V | 10K [2] | Open Circuit | 10K | 42 |
| 5V | 0 | Open Circuit | 120 | 64 |
| | | | 470 | 82 |
| | | | 10K | 112 |

[2] With Vdd= 3V and Rbias < 10K Ohm may result in the part becoming conditionally unstable which is not recommended.

Absolute Maximum Ratings

| | |
|---|----------------|
| Drain Bias Voltage (Vdd) | 6V |
| RF Input Power (RFIN) (Vdd = +5 Vdc) | +10 dBm |
| Channel Temperature | 150 °C |
| Continuous Pdiss (T= 85 °C) (derate 19.35 mW/°C above 85 °C) | 1.26 W |
| Thermal Resistance (channel to ground paddle) | 51.67 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |

**Typical Supply
Current vs. Vdd (R_{bias} = 10K)**

| Vdd (V) | Idd (mA) |
|---------|----------|
| 2.7 | 31 |
| 3.0 | 42 |
| 3.3 | 52 |
| 4.5 | 95 |
| 5.0 | 112 |
| 5.5 | 129 |

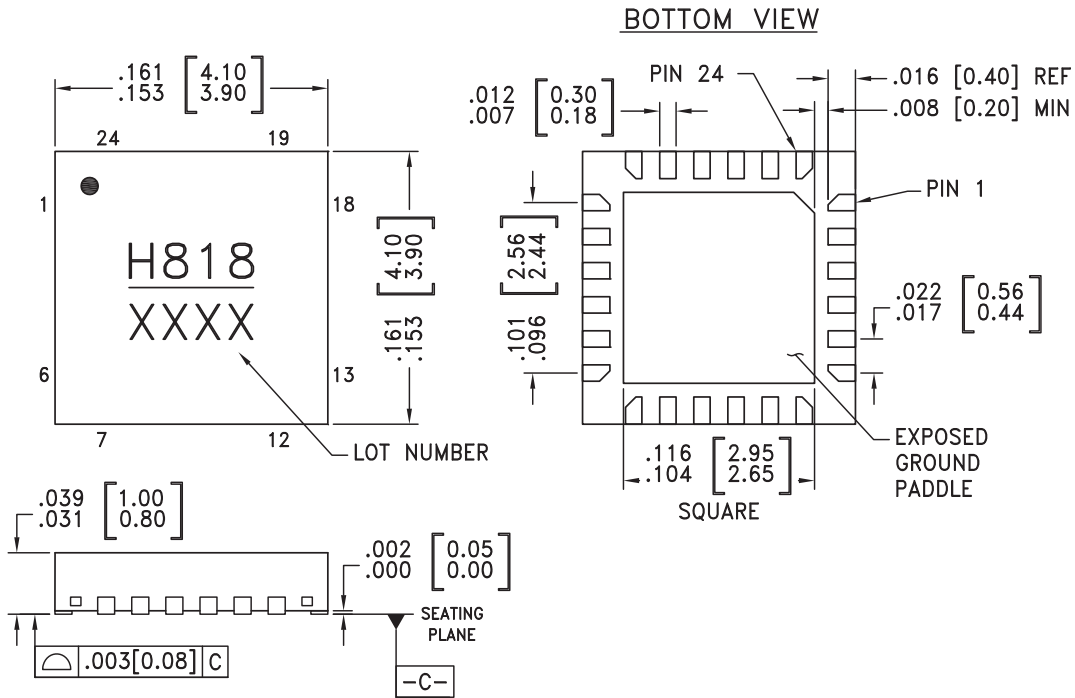
Note: Amplifier will operate over full voltage ranges shown above.



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

[1] Vdd = 5V

Outline Drawing





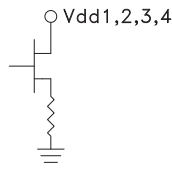
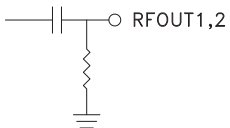
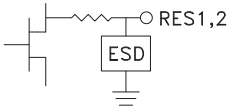
Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[1] |
|-------------|---|---------------|---------------------|--------------------------------|
| HMC818LP4E | RoHS-compliant Low Stress Injection Molding Plastic | 100% matte Sn | MSL1 ^[2] | 818 XXXX |

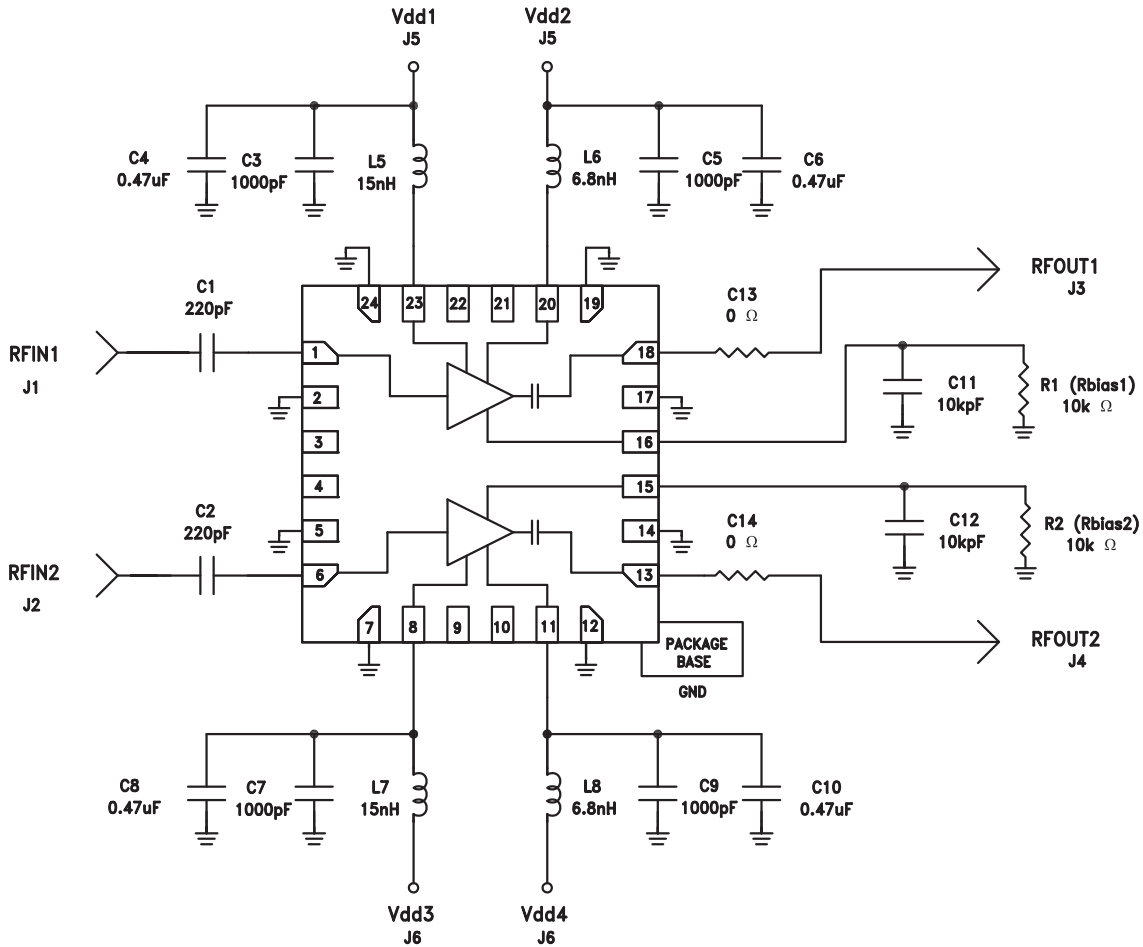
[1] 4-Digit lot number XXXX

[2] Max peak reflow temperature of 235 °C

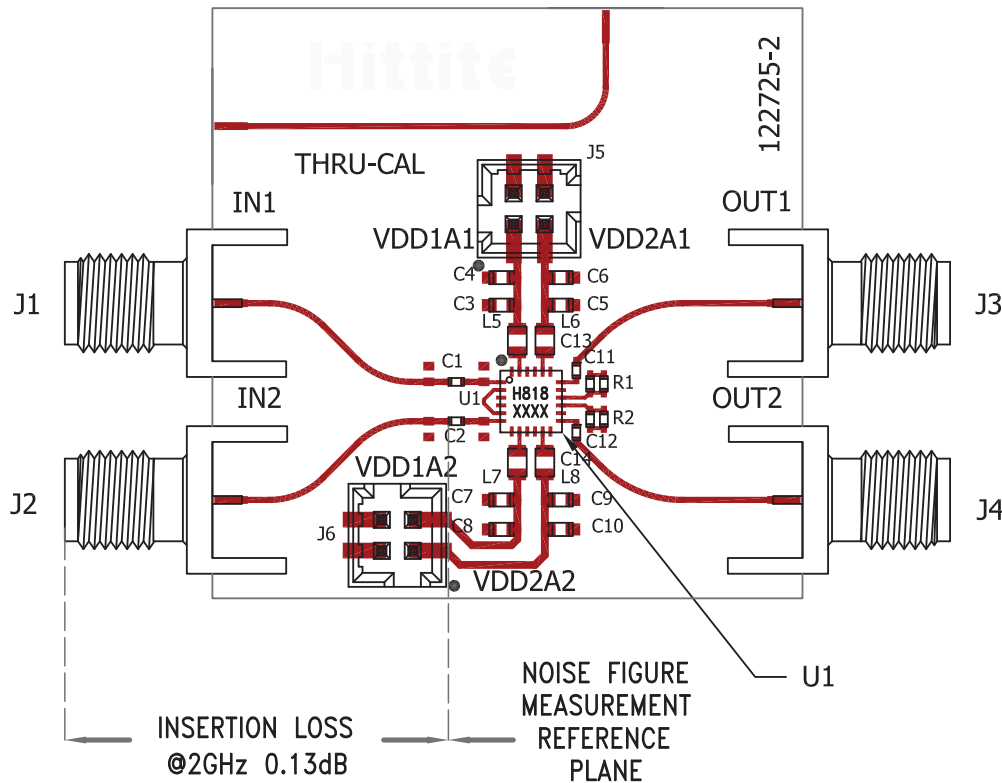

Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|-----------------------------|---------------|--|---|
| 1, 6 | RFIN1, 2 | This pin is DC coupled an off chip DC blocking capacitor is required. | RFIN1,2  |
| 2, 5, 7, 12, 14, 17, 19, 24 | GND | Package bottom must be connected to RF/DC ground. |  |
| 3, 4, 9, 10, 21, 22 | N/C | No connection required. These pins may be connected to RF/DC ground without affecting performance. | |
| 23, 20, 8, 11 | Vdd1, 2, 3, 4 | Power supply voltage for each amplifier. Choke inductor and bypass capacitors are required. See application circuit. |  |
| 18, 13 | RFOUT1, 2 | This pin is matched to 50 Ohms. |  |
| 16, 15 | RES1, 2 | These pins are used to set the DC current Idd2 and Idd4 in each amplifier via an external biasing resistor. See application circuit. |  |

Application Circuit



Evaluation PCB



List of Materials for Evaluation PCB 122727 [1]

| Item | Description |
|---------------------|-----------------------------------|
| J1 - J4 | PCB Mount SMA RF Connector |
| J5, J6 | 2mm Vertical Molex 8pos Connector |
| C1, C2 | 220 pF Capacitor, 0402 Pkg.. |
| C3, C5, C7, C9 | 1000 pF Capacitor, 0603 Pkg. |
| C4, C6, C8, C10 | 0.47 μ F Capacitor, 0603 Pkg. |
| C11, C12 | 10 kpF Capacitor, 0402 Pkg. |
| C13, C14 | 0 Ohm Resistor, 0402 Pkg. |
| L5, L7 | 15 nH Inductor, 0603 Pkg. |
| L6, L8 | 6.8 nH Inductor, 0603 Pkg. |
| R1, R2 (Rbias 1, 2) | 10k Ohm Resistor, 0402 Pkg. |
| U1 | HMC818LP4(E) Amplifier |
| PCB [2] | 122725 Evaluation PCB |

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350 or Arlon 25FR

The circuit board used in this application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.